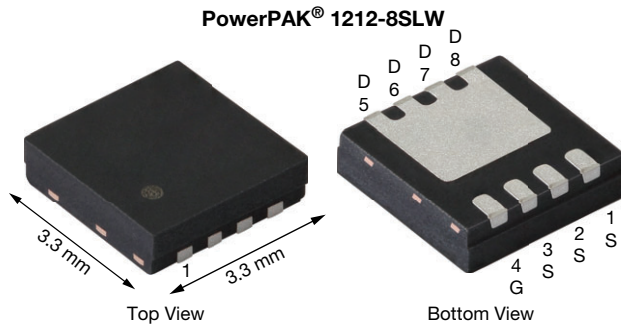


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

 AUTOMOTIVE
GRADE

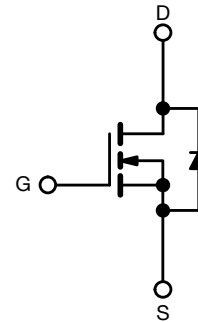
RoHS
COMPLIANT
HALOGEN
FREE
FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Wettable flank terminals
- Low thermal resistance with 0.75 mm profile
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



Marking code: Q042

PRODUCT SUMMARY	
V _{DS} (V)	40
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.00253
I _D (A)	214
Configuration	Single
Package	PowerPAK 1212-8SLW



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-source voltage	V _{DS}		40	V
Gate-source voltage	V _{GS}		± 20	
Continuous drain current	T _C = 25 °C		214	A
	T _C = 125 °C		123	
Continuous source current (diode conduction)	I _S		179	
Pulsed drain current ^a	I _{DM}		350	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	31.5	mJ
Single pulse avalanche energy		E _{AS}	49.6	
Maximum power dissipation ^a	T _C = 25 °C		197	W
	T _C = 125 °C		65	
Operating junction and storage temperature range	T _J , T _{stg}		-55 to +175	°C
Soldering recommendations (peak temperature) ^c			260	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL		LIMIT	UNIT
Junction-to-ambient	PCB mount ^b		81	°C/W
Junction-to-case (drain)	R _{thJC}		0.76	

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.5	3.0	3.5	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 40\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	20	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$	-	0.0021	0.00253	Ω
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.0038	
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.0043	
Forward transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		-	55	-	S
Dynamic ^b							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	2222	3111	pF
Output capacitance	C_{oss}			-	923	1295	
Reverse transfer capacitance	C_{rss}			-	37	52	
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 20\text{ V}, I_D = 5\text{ A}$	-	38	57	nC
Gate-source charge ^c	Q_{gs}			-	11	-	
Gate-drain charge ^c	Q_{gd}			-	8	-	
Gate resistance	R_g	f = 1 MHz		0.5	1.1	1.7	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 1.33\text{ }\Omega$ $I_D \cong 15\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	13	20	ns
Rise time ^c	t_r			-	5	9	
Turn-off delay time ^c	$t_{d(off)}$			-	22	33	
Fall time ^c	t_f			-	8	12	
Source-Drain Diode Ratings and Characteristic ^b							
Pulsed current ^a	I_{SM}			-	-	350	A
Forward voltage	V_{SD}	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$		-	0.82	1.1	V
Body diode reverse recovery time	t_{rr}	$I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		-	38	78	ns
Body diode reverse recovery charge	Q_{rr}			-	34	70	nC
Reverse recovery fall time	t_a			-	19	-	ns
Reverse recovery rise time	t_b			-	20	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-1.6	-3.2	A

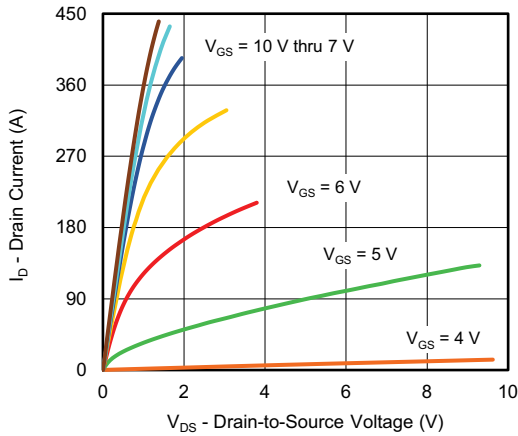
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

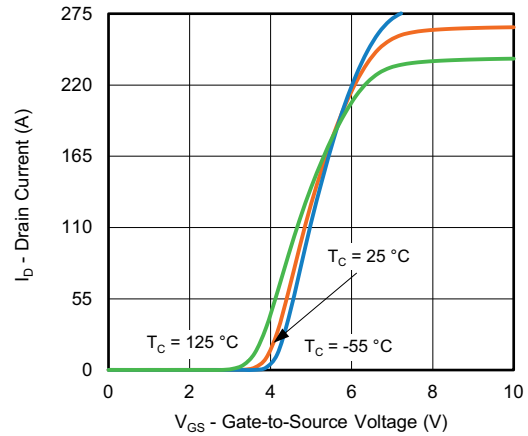
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



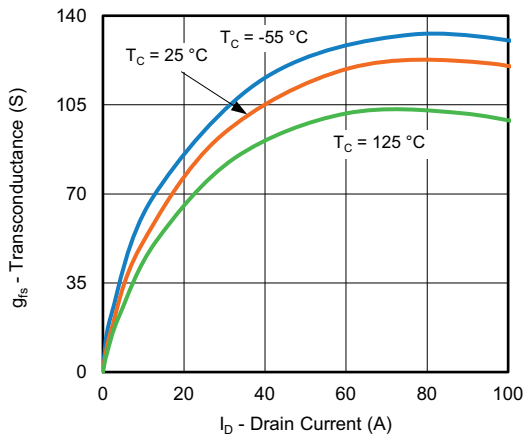
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



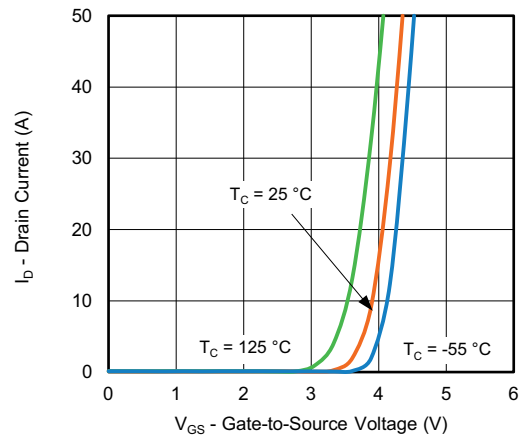
Output Characteristics



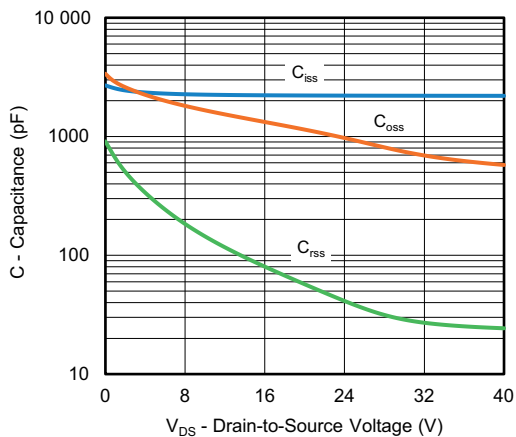
Transfer Characteristics



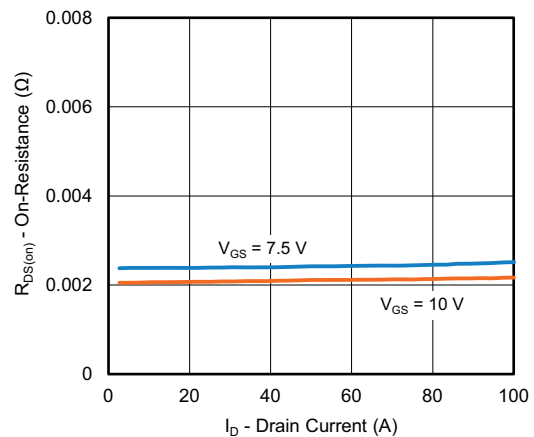
Transconductance



Transfer Characteristics

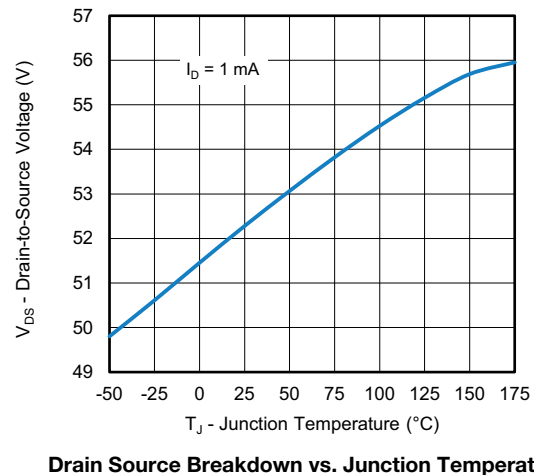
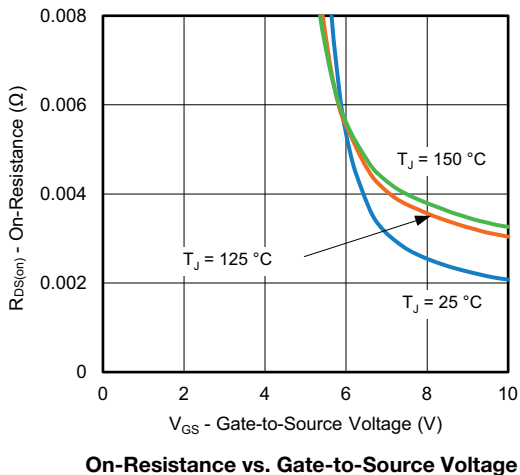
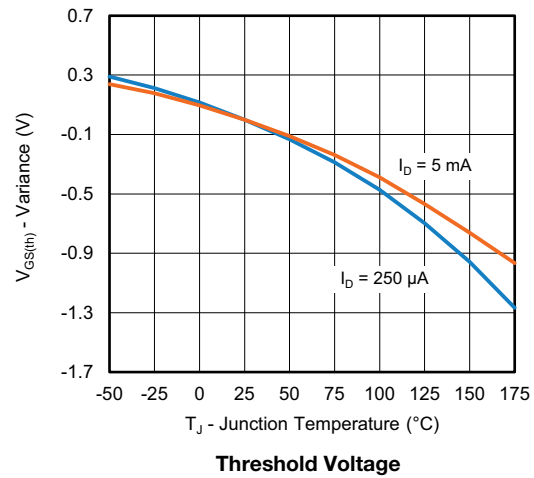
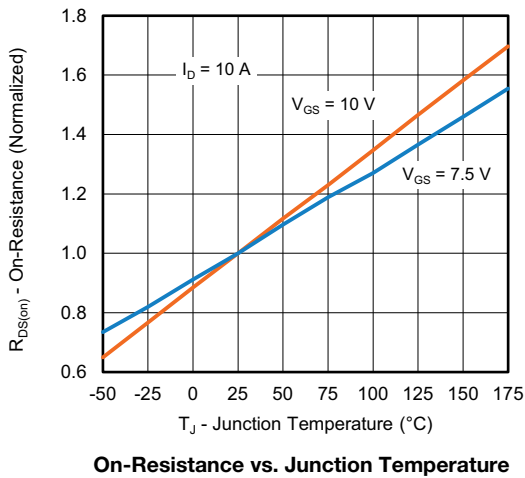
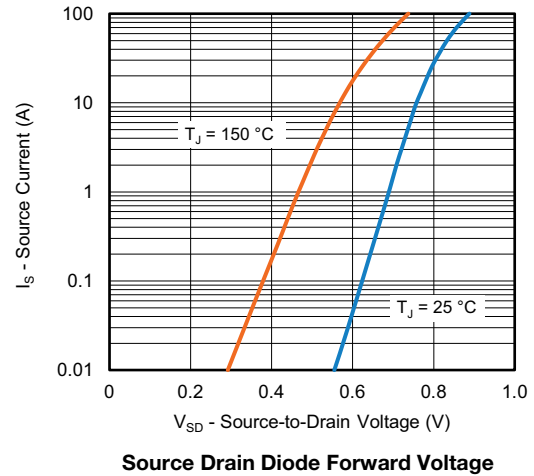
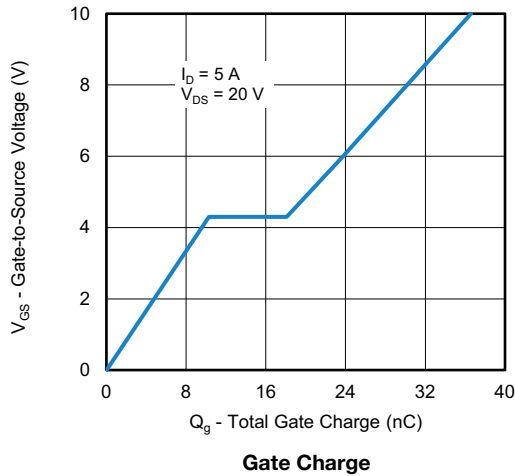


Capacitance



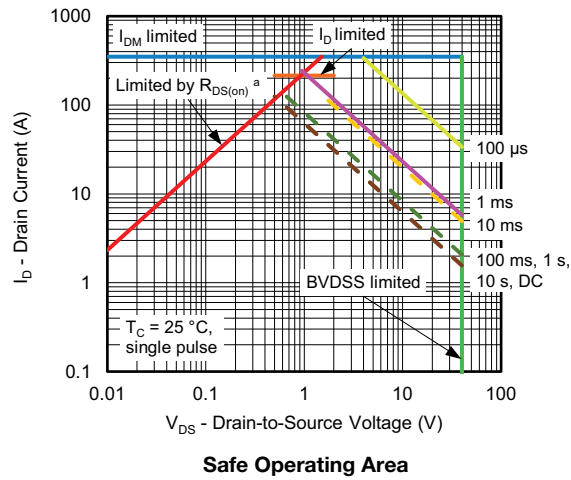
On-Resistance vs. Drain Current

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

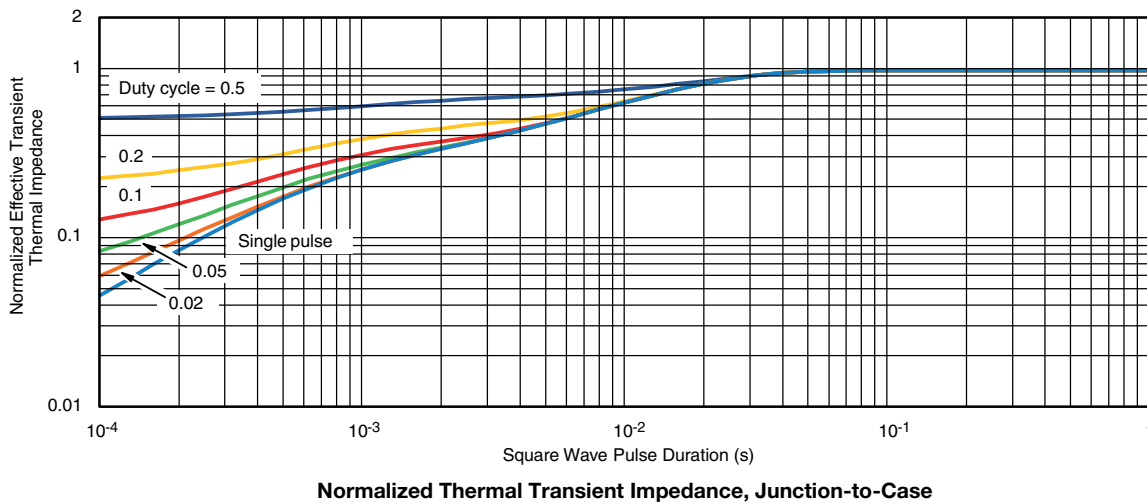
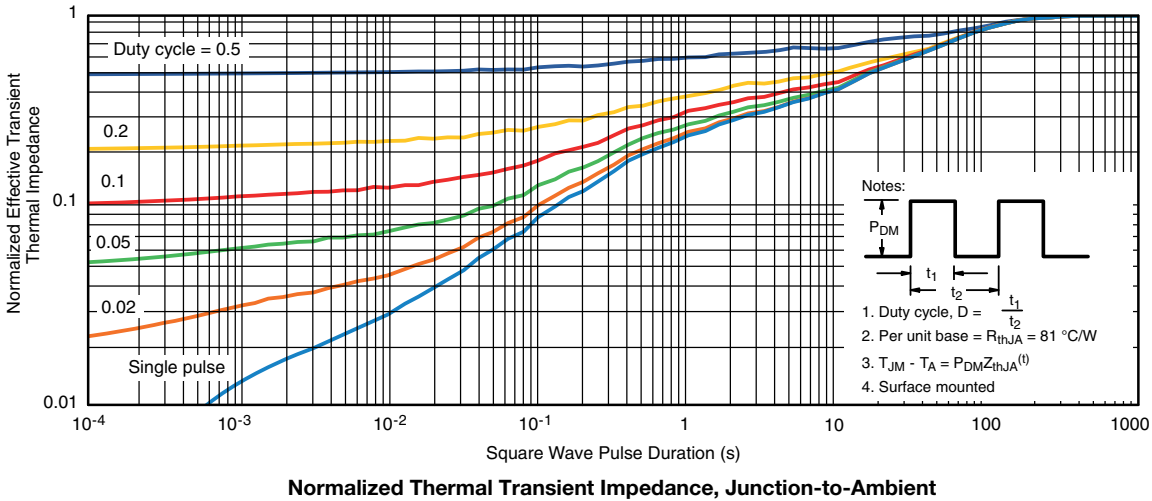


Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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